Implementation of 64-bit Decimal Matrix Code for correcting Cell Upsets in Static Random Access Memories

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Abstract: In this paper, novel per-word 64-bit DMC was proposed to assure the reliability of memory. Here to detect and correct maximum 32 errors. The proposed protection code utilized decimal algorithm to detect errors, so that more errors were detected and corrected. The obtained results showed that the proposed scheme has a superior protection level against large MCUs in memory. Besides, the proposed decimal error detection technique is an attractive opinion to detect MCUs in CAM because it can be combined with BICS to provide an adequate level of immunity. Transient multiple cell upsets (MCUs) are becoming major issues in the reliability of memories exposed to radiation environment. To prevent MCUs from causing data corruption, more complex error correction codes (ECCs) are widely used to protect memory, but the main problem is that they would require higher delay overhead. Recently, matrix codes (MCs) based on Hamming codes have been proposed for memory protection. The main issue is that they are double error correction codes and the error correction capabilities are not improved in all cases. Moreover, the encoder-reuse technique (ERT) is proposed to minimize the area overhead of extra circuits without disturbing the whole encoding and decoding processes. ERT uses DMC encoder itself to be part of the decoder.

Keywords: Error correction codes (ECCs), mean time to failure (MTTF), memory, multiple cells upsets (MCUs).

1. INTRODUCTION

As CMOS technology scales down to nano-scale and memories are combined with an increasing number of electronic systems, the soft error rate in memory cells is rapidly increasing, especially when memories operate in space environments due to ionizing effects of atmospheric neutron, alpha-particle, and cosmic rays.

Although single bit upset is a major concern about memory reliability, multiple cell upsets (MCUs) have become a serious reliability concern in some memory applications. In order to make memory cells as fault-tolerant as possible, some error correction codes (ECCs) have been widely used to protect memories against soft errors for years. For example, the Bose–Chaudhuri–Hocquenghem codes, Reed–Solomon codes, and punctured difference set (PDS) codes have been used to deal with MCUs in memories. But these codes require more area, power, and delay overheads since the encoding and decoding circuits are more complex in these complicated codes.

Interleaving technique has been used to restrain MCUs, which rearrange cells in the physical arrangement to separate the bits in the same logical word into different physical words. However, interleaving technique may not be practically used in content-addressable memory (CAM), because of the tight coupling of hardware structures from both cells and comparison circuit structures.

Built-in current sensors (BICS) are proposed to assist with single-error correction and double-error detection codes to provide protection against MCUs. However, this technique can only correct two errors in a word.

More recently, in 2-D matrix codes (MCs) are proposed to efficiently correct MCUs per word with a low decoding delay, in which one word is divided into multiple rows and multiple columns in logical. The bits per row are protected by Hamming code, while parity code is added in each column. For the MC based on Hamming, when two errors are detected by Hamming, the vertical syndrome bits are
activated so that these two errors can be corrected. As a result, MC is capable of correcting only two errors in all cases. In an approach that combines decimal algorithm with Hamming code has been conceived to be applied at software level. It uses addition of integer values to detect and correct soft errors. The results obtained have shown that this approach have a lower delay overhead over other codes.

In this paper, novel decimal matrix code (DMC) based on divide-symbol is proposed to provide enhanced memory reliability. The proposed DMC utilizes decimal algorithm (decimal integer addition and decimal integer subtraction) to detect errors. The advantage of using decimal algorithm is that the error detection capability is maximized so that the reliability of memory is enhanced. Besides, the encoder-reuse technique (ERT) is proposed to minimize the area overhead of extra circuits (encoder and decoder) without disturbing the whole encoding and decoding processes, because ERT uses DMC encoder itself to be part of the decoder.

Fig1. Proposed schematic of fault-tolerant memory protected with DMC.

This paper is divided into the following sections. The proposed DMC is introduced and its encoder and decoder circuits are present in Section II. The simulation outputs are in section III. Finally, some conclusions of this paper are discussed and shared.

2. PROPOSED DMC

In this section, DMC is proposed to assure reliability in the presence of MCUs with reduced performance overheads, and a 64-bit word is encoded and decoded as an example based on the proposed techniques.

2.1. Proposed Schematic of Fault-Tolerant Memory

The proposed schematic of fault-tolerant memory is depicted in Fig. First, during the encoding (write) process, information bits D are fed to the DMC encoder, and then the horizontal redundant bits H and vertical redundant bits V are obtained from the DMC encoder. When the encoding process is completed, the obtained DMC codeword is stored in the memory. If MCUs occur in the memory, these errors can be corrected in the decoding (read) process. Due to the advantage of decimal algorithm, the proposed DMC has higher fault-tolerant capability with lower performance overheads. In the fault-tolerant memory, the ERT technique is proposed to reduce the area overhead of extra circuits and will be introduced in the following sections.

2.2. Proposed DMC Encoder

In the proposed DMC, first, the divide-symbol and arrange-matrix ideas are performed, i.e., the N-bit word is divided into k symbols of m bits (N = k \times m), and these symbols are arranged in a k1 \times k2 2-D matrix (k = k1 \times k2, where the values of k1 and k2 represent the numbers of rows and columns in
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the logical matrix respectively). Second, the horizontal redundant bits $H$ are produced by performing decimal integer addition of selected symbols per row. Here, each symbol is regarded as a decimal integer. Third, the vertical redundant bits $V$ are obtained by binary operation among the bits per column. It should be noted that both divide-symbol and arrange-matrix are implemented in logical instead of in physical. Therefore, the proposed DMC does not require changing the physical structure of the memory.

To explain the proposed DMC scheme, we take a 64-bit word as an example, as shown in Fig. 2. The cells from D0 to D63 are information bits. This 64-bit word has been divided into sixteen symbols of 4-bit. $k1 = 2$ and $k2 = 4$ have been chosen simultaneously. H0–H39 are horizontal check bits; V0 through V31 are vertical check bits. However, it should be mentioned that the maximum correction capability (i.e., the maximum size of MCUs can be corrected) and the number of redundant bits are different when the different values for $k$ and $m$ are chosen. Therefore, $k$ and $m$ should be carefully adjusted to maximize the correction capability and minimize the number of redundant bits. For example, in this case, when $k = 2 \times 2$ and $m = 8$, only 1-bit error can be corrected and the number of redundant bits is 80. When $k = 4 \times 4$ and $m = 2$, 3-bit errors can be corrected and the number of redundant bits is reduced to 32. However, when $k = 2 \times 4$ and $m = 4$, the maximum correction capability is up to 5 bits and the number of redundant bits is 72. In this paper, in order to enhance the reliability of memory, the error correction capability is first considered, so $k = 2 \times 8$ and $m = 4$ are utilized to construct DMC.

The horizontal redundant bits $H$ can be obtained by decimal integer addition as follows:

$H4H3H2H1H0 = D3D2D1D0 + D19D18D17D16 \quad (1)$

$H9H8H7H6H5 = D7D6D5D4 + D23D22D21D20 \quad (2)$


For the vertical redundant bits $V$, we have

$V0 = D0 \wedge D31 \quad (3)$

$V1 = D1 \wedge D32 \quad (4)$

And similarly for the rest vertical redundant bits

The encoding can be performed by decimal and binary addition operations from (1) to (4). The encoder that computes the redundant bits using multibit adders and XOR gates is shown in Fig. In this figure, H39 – H0 are horizontal redundant bits, V31 – V0 are vertical redundant bits, and the remaining bits U63 – U0 are the information bits which are directly copied from D31 to D0. The enable signal En will be explained in the next section.

2.3. Proposed DMC Decoder

To obtain a word being corrected, the decoding process is required. For example, first, the received redundant bits $H4H3H2H1H0'$ and $V0'–V3'$ are generated by the received information bits $D'$. Second, the horizontal syndrome bits $\Delta H4H3H2H1H0$ and the vertical syndrome bits $S3 – S0$ can be calculated as follows:

$\Delta H4H3H2H1H0 = H4H3H2H1H0' – H4H3H2H1H0 \quad (5)$

$S0 = V0' \wedge V0 \quad (6)$

And similarly for the rest vertical syndrome bits, where “−” represents decimal integer subtraction. When $\Delta H4H3H2H1H0$ and $S3 – S0$ are equal to zero, the stored codeword has original information bits in symbol 0 where no errors occur. When $\Delta H4H3H2H1H0$ and $S3 – S0$ are nonzero, the induced errors (the number of errors is 4 in this case) are detected and located in symbol 0, and then these errors can be corrected by

$D0\text{correct} = D0 \wedge S0 \quad (7)$
Fig2. 64-bits DMC logical organization \((k = 2 \times 8\) and \(m = 4\)). Here, each symbol is regarded as a decimal integer.

Fig3. 64-bit DMC encoder structure using multi bit adders and XOR gates.

Fig 4. 64-bit DMC decoder structure using ERT.
The proposed DMC decoder is depicted in Fig, which is made up of the following sub modules, and each executes a specific task in the decoding process: syndrome calculator, error locator, and error corrector. It can be observed from this figure that the redundant bits must be recomputed from the received information bits $D'$ and compared to the original set of redundant bits in order to obtain the syndrome bits $\Delta H$ and $S$. Then error locator uses $\Delta H$ and $S$ to detect and locate which bits some errors occur in. Finally, in the error corrector, these errors can be corrected by inverting the values of error bits.

In the proposed scheme, the circuit area of DMC is minimized by reusing its encoder. This is called the ERT. The ERT can reduce the area overhead of DMC without disturbing the whole encoding and decoding processes. From Fig, it can be observed that the DMC encoder is also reused for obtaining the syndrome bits in DMC decoder. Therefore, the whole circuit area of DMC can be minimized as a result of using the existent circuits of encoder. Besides, this figure also shows the proposed decoder with an enable signal $E_n$ for deciding whether the encoder needs to be a part of the decoder. In other words, the $E_n$ signal is used for distinguishing the encoder from the decoder, and it is under the control of the write and read signals in memory. Therefore, in the encoding (write) process, the DMC encoder is only an encoder to execute the encoding operations. However, in the decoding (read) process, this encoder is employed for computing the syndrome bits in the decoder. These clearly show how the area overhead of extra circuits can be substantially reduced.

3. Simulation Results
RTL Schematic diagram

Technology schematic
4. CONCLUSION

To prevent MCUs from causing data corruption, more complex error correction codes (ECCs) are widely used to protect memory, but the main problem is that they would require higher delay overhead. Recently, matrix codes (MCs) based on Hamming codes have been proposed for memory protection.

In this paper, novel per-word DMC was proposed to assure the reliability of memory. The proposed protection code utilized decimal algorithm to detect errors, so that more errors were detected and
corrected. The obtained results showed that the proposed scheme has a superior protection level against large MCUs in memory. Besides, the proposed decimal error detection technique is an attractive opinion to detect MCUs in CAM because it can be combined with BICS to provide an adequate level of immunity.

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